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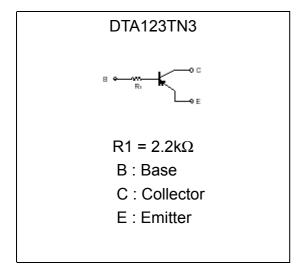
**PNP Digital Transistors (Built-in Resistors)** 



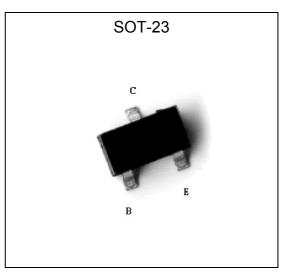
## Features

- •Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- •The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- •Only the on/off conditions need to be set for operation, making device design easy.
- •Complements the DTC123TN3

# **Equivalent Circuit**



# Outline



### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	Vcbo	-50	V
Collector-Emitter Voltage	VCEO	-50	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current	Ic	-100	mA
Power Dissipation	Pd	200	mW
Thermal Resistance, Junction to Ambient	Roja	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C



# Characteristics (Ta=25°C)

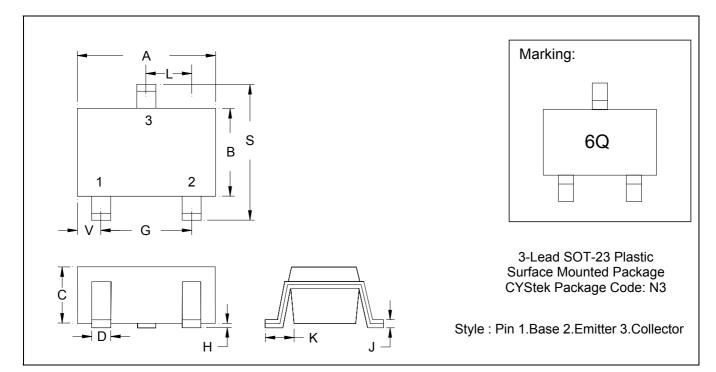
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	ВУсво	-50	-	-	V	Ic=-50μA
Collector-Emitter Breakdown Voltage	BVCEO	-50	-	-	V	Ic=-1mA
Emitter-Base Breakdown Voltage	BVebo	-5	-	-	V	IE=-50μA
Collector-Base Cutoff Current	Ісво	-	-	-0.5	μΑ	$V_{CB}=-50V$
Emitter-Base Cutoff Current	Iebo	-	-	-0.5	μA	$V_{EB}=-4V$
Collector-Emitter Saturation Voltage	VCE(sat)	-	0.1	-0.3	V	Ic=-5mA, IB=-0.25mA
DC Current Gain	hfe	100	-	600	-	VCE=-5V, IC=-1mA
Input Resistance	R	1.54	2.2	2.86	kΩ	-
Transition Frequency	fт	-	250	-	MHz	Vce=-10V, Ic=-5mA, f=100MHz*

\* Transition frequency of the device



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#### **SOT-23 Dimension**



\*:Tvpical

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DIM	Inches Millimet		neters	DIM	Inches		Millimeters		
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
В	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
С	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
Н	0.0005	0.0040	0.013	0.10					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material. 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

• Lead : 42 Alloy ; solder plating

• Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0

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